MA6S718

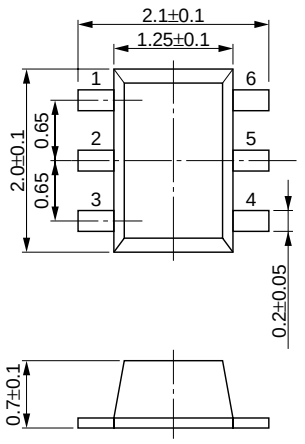
Silicon epitaxial planer type

For the switching circuit

■ Features

- Small S-Mini 6-pin package
- Independent three-element incorporated, enabling high density mounting
- Flat lead type, helping improvement of the actual mounting ratio and solderability of a high-speed mounter
- Low forward voltage V_F, optimum for low-voltage rectification
- Fast reverse recovery time t_{rr}, optimum for high-frequency rectification

Unit : mm



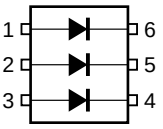
1 : Anode 1 4 : Cathode 3
2 : Anode 2 5 : Cathode 2
3 : Anode 3 6 : Cathode 1
S-Mini Type Package (6-pin)

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Peak reverse voltage	V_{RM}	30	V
Peak forward current	I_{FM}	150*	mA
Forward current (DC)	I_F	30*	mA
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to + 125	˚C

* Value in single diode used

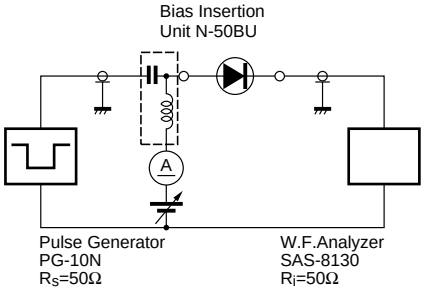
■ Internal Connection

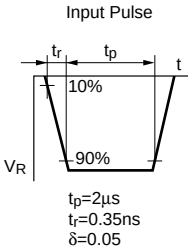


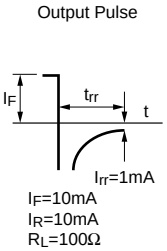
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R = 30V			1	μA
Forward voltage (DC)	V_{F1}	I_F =1mA			0.4	V
	V_{F2}	I_F = 30mA			1	V
Terminal capacitance	C_t	V_R =1V, f=1MHz		1.5		pF
Reverse recovery time	t_{rr}*	I_F = I_R=10mA I_{rr}=1mA, R_L=100Ω		1		ns
Detection efficiency	η	V_{in}= 3$V_{(peak)}$, f= 30MHz R_L= 3.9kΩ, C_L=10pF		65		%

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 2000MHz
3. * t_{rr} measuring circuit







■ Marking